



SANYO Semiconductors

DATA SHEET

VEC2812

MOSFET : N-Channel Silicon MOSFET

SBD : Schottky Barrier Diode

General-Purpose Switching Device
Applications

Features

- DC / DC converter.
- Composite type with an N-channel silicon MOSFET and a schottky barrier diode contained in one package facilitating high-density mounting.
- [MOSFET]
 - Low ON-resistance.
 - 1.8V drive.
- [SBD]
 - Short reverse recovery time.
 - Low forward voltage.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
[MOSFET]				
Drain-to-Source Voltage	V _{DSS}		20	V
Gate-to-Source Voltage	V _{GSS}		±10	V
Drain Current (DC)	I _D		1.5	A
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	6	A
Allowable Power Dissipation	P _D	Mounted on a ceramic board (900mm ² X0.8mm) 1unit	0.8	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +125	°C
[SBD]				
Repetitive Peak Reverse Voltage	V _{RRM}		30	V
Nonrepetitive Peak Reverse Surge Voltage	V _{RSM}		35	V
Average Output Current	I _O		1	A
Surge Forward Current	I _{FSM}	50Hz sine wave, 1 cycle	10	A
Junction Temperature	T _J		-55 to +125	°C
Storage Temperature	T _{stg}		-55 to +125	°C

Marking : BZ

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VEC2812

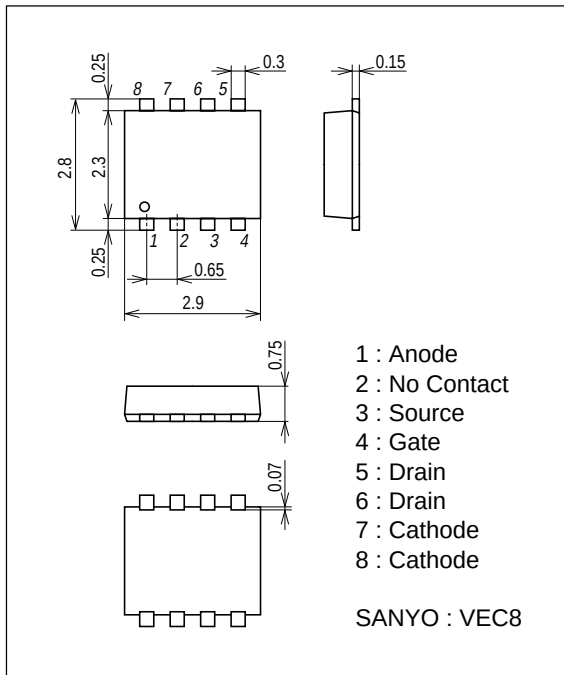
Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
[MOSFET]						
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	20			V
Zero-Gate Voltage Drain Current	IDSS	VDS=20V, VGS=0V			1	μA
Gate-to-Source Leakage Current	IGSS	VGSS=±8V, VDS=0V			±10	μA
Cutoff Voltage	VGS(off)	VDS=10V, ID=1mA	0.4		1.3	V
Forward Transfer Admittance	yfs	VDS=10V, ID=1A	1.7	2.8		S
Static Drain-to-Source On-State Resistance	RDS(on)1	ID=1A, VGS=4V		160	210	mΩ
	RDS(on)2	ID=0.5A, VGS=2.5V		220	290	mΩ
	RDS(on)3	ID=0.1A, VGS=1.8V		310	435	mΩ
Input Capacitance	Ciss	VDS=10V, f=1MHz		100		pF
Output Capacitance	Coss	VDS=10V, f=1MHz		22		pF
Reverse Transfer Capacitance	Crss	VDS=10V, f=1MHz		15		pF
Turn-ON Delay Time	td(on)	See specified Test Circuit.		5.5		ns
Rise Time	tr	See specified Test Circuit.		18		ns
Turn-OFF Delay Time	td(off)	See specified Test Circuit.		17		ns
Fall Time	tf	See specified Test Circuit.		8		ns
Total Gate Charge	Qg	VDS=10V, VGS=10V, ID=1.5A		4.5		nC
Gate-to-Source Charge	Qgs	VDS=10V, VGS=10V, ID=1.5A		0.4		nC
Gate-to-Drain “Miller” Charge	Qgd	VDS=10V, VGS=10V, ID=1.5A		0.4		nC
Diode Forward Voltage	VSD	IS=1.5A, VGS=0V		0.9	1.2	V
[SBD]						
Reverse Voltage	VR	IR=500μA	30			V
Forward Voltage	VF1	IF=500mA		0.35	0.39	V
	VF2	IF=1A		0.4	0.45	V
Reverse Current	IR	VR=15V			360	μA
Interterminal Capacitance	C	VR=10V, f=1MHz		27		pF
Reverse Recovery Time	trr	IF=IR=100mA, See specified Test Circuit.			10	ns

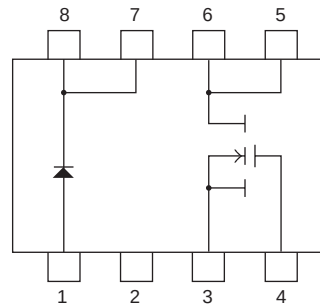
Package Dimensions

unit : mm (typ)

7012-004



Electrical Connection



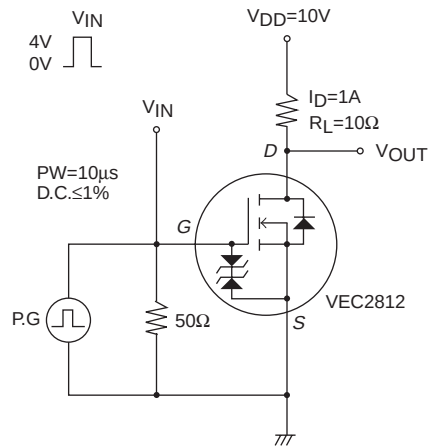
- 1 : Anode
- 2 : No Contact
- 3 : Source
- 4 : Gate
- 5 : Drain
- 6 : Drain
- 7 : Cathode
- 8 : Cathode

Top view

VEC2812

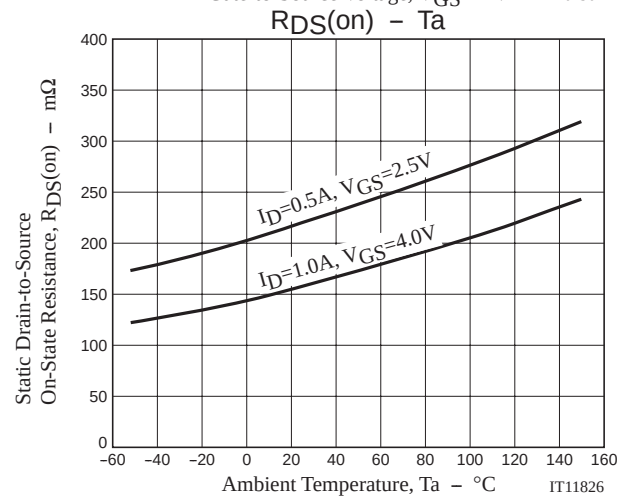
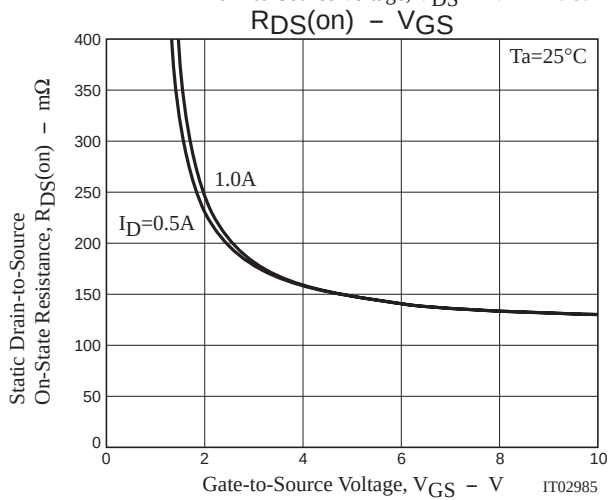
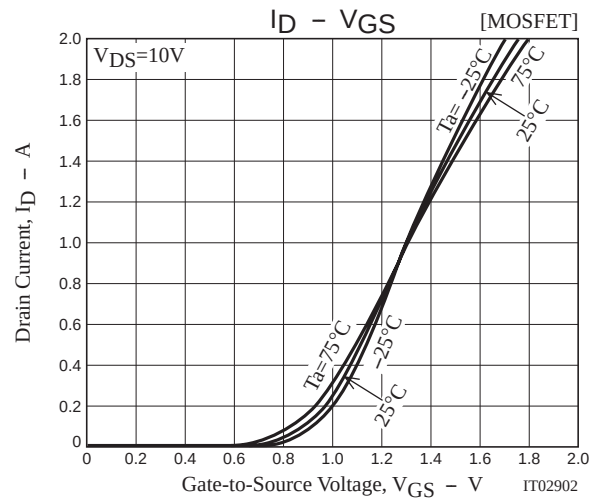
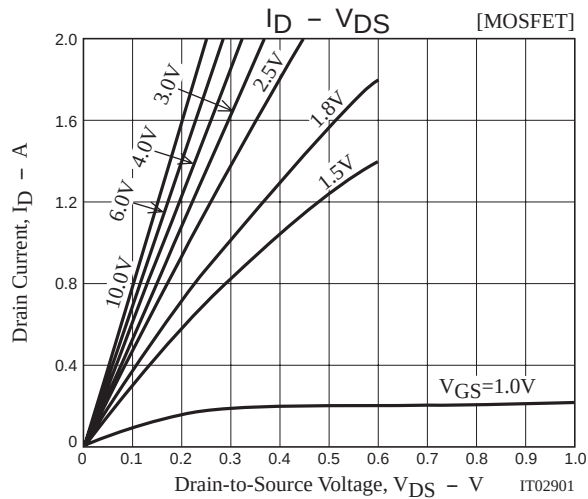
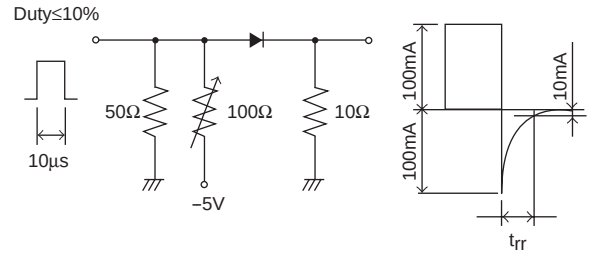
Switching Time Test Circuit

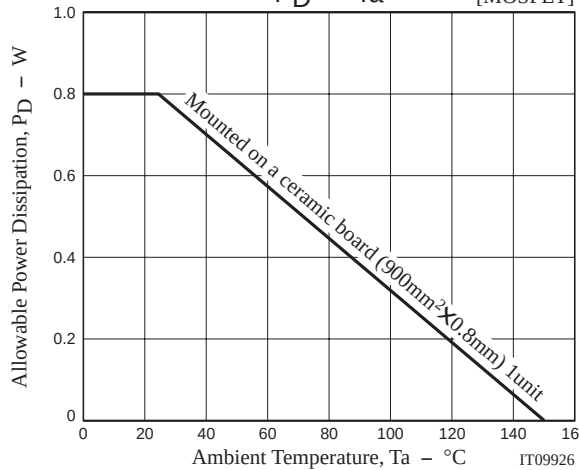
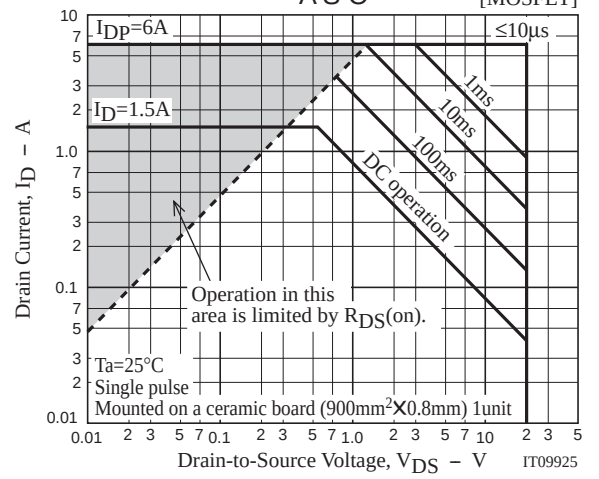
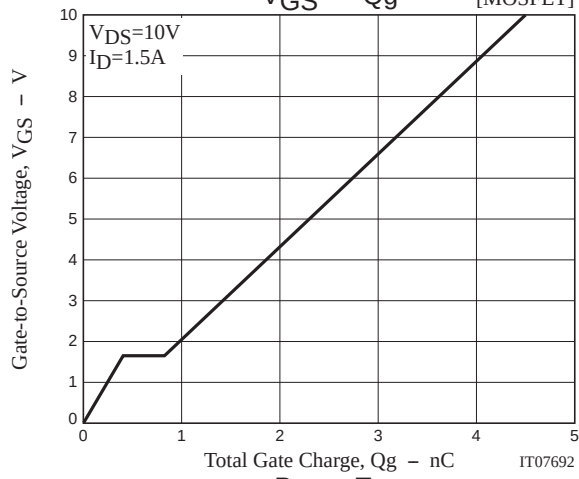
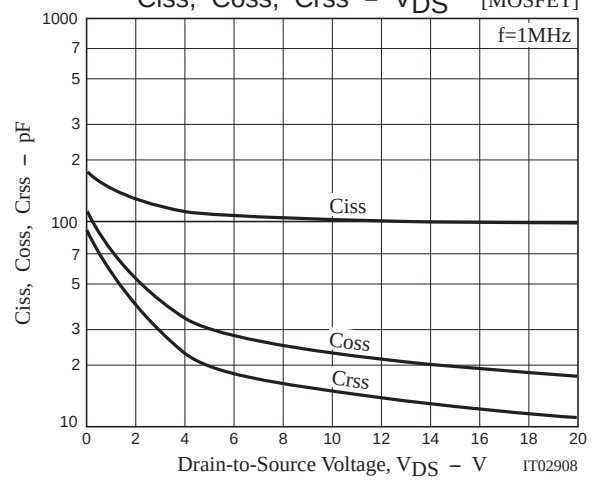
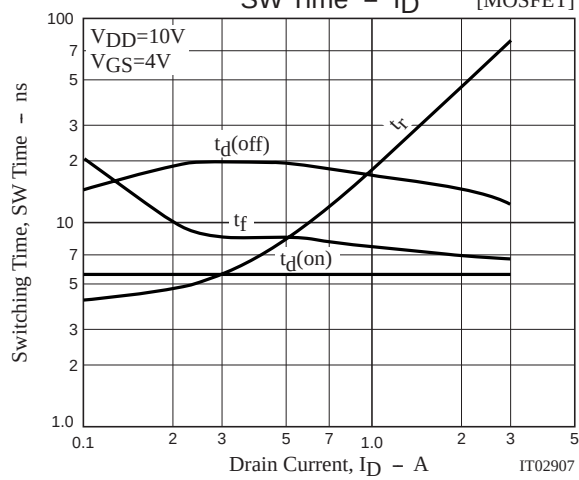
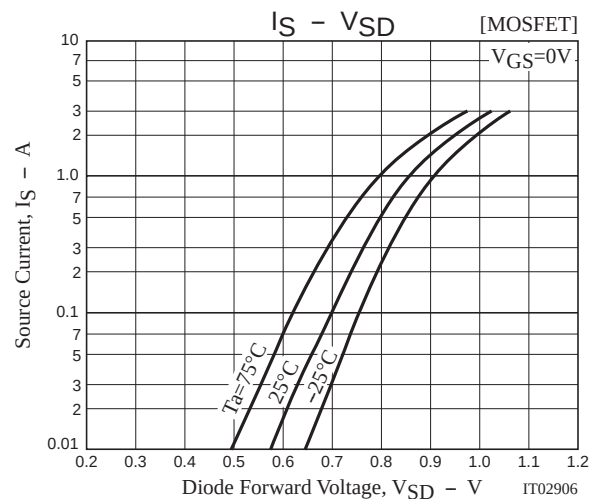
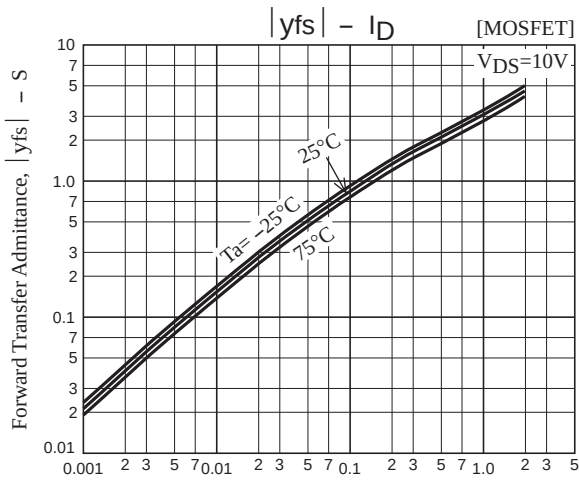
[MOSFET]

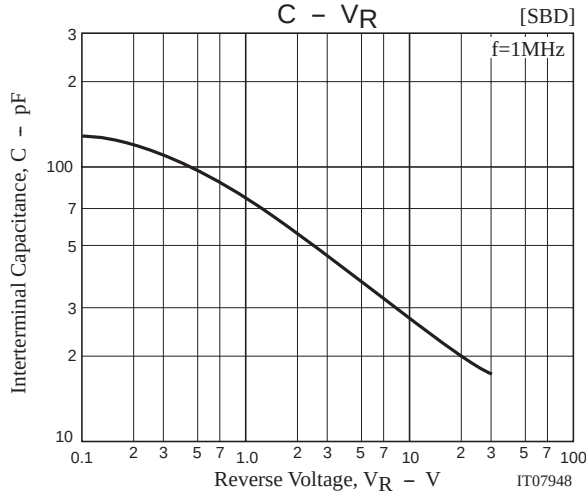
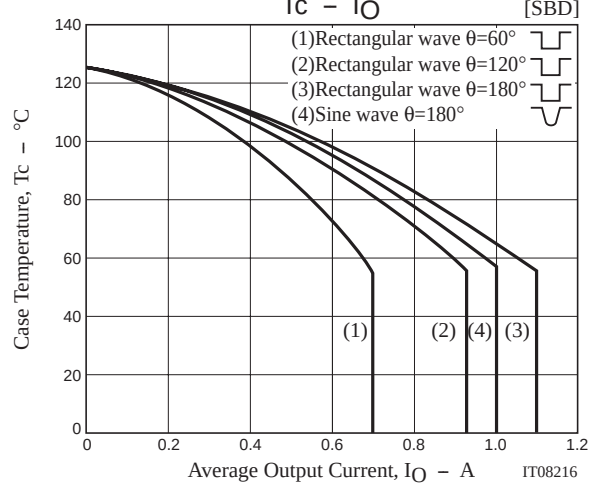
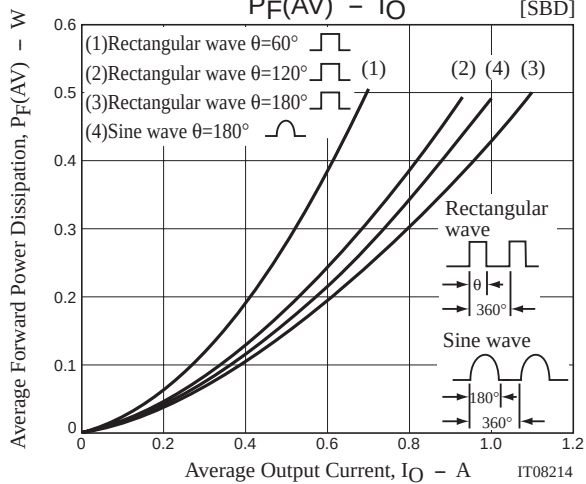
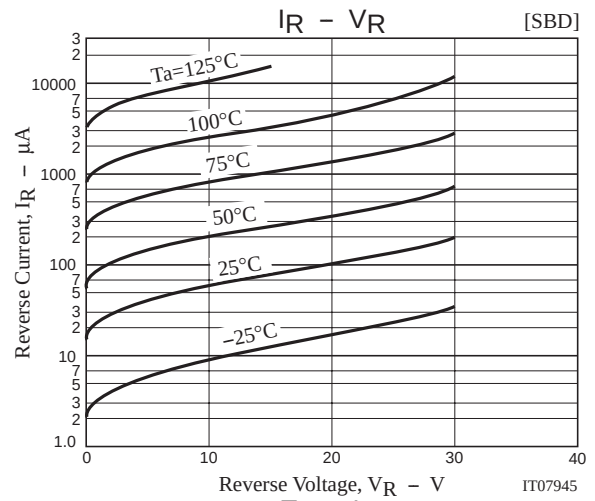
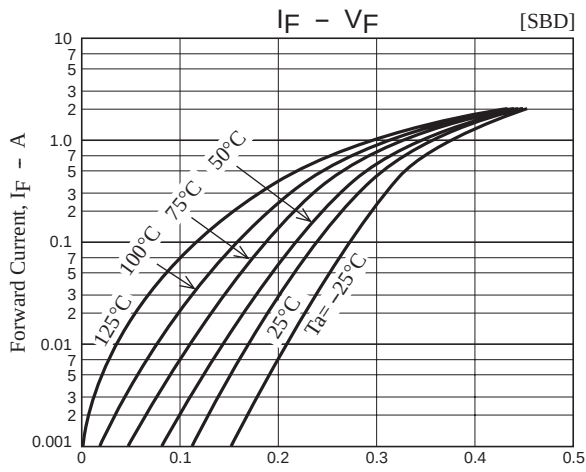


t_{rr} Test Circuit

[SBD]







Note on usage : Since the VEC2812 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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